

Michele Perego

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

133
papers

2,635
citations

30
h-index

42
g-index

147
ext. papers

2,948
ext. citations

4.5
avg, IF

4.81
L-index

#	Paper	IF	Citations
133	Study of recrystallization and activation processes in thin and highly doped silicon-on-insulator layers by nanosecond laser thermal annealing. <i>Journal of Applied Physics</i> , 2022 , 131, 065301	2.5	0
132	Inside the brush: partition by molecular weight in grafting to reactions from melt. <i>Polymer Chemistry</i> , 2021 , 12, 6538-6547	4.9	2
131	Engineering of the spin on dopant process on silicon on insulator substrate. <i>Nanotechnology</i> , 2021 , 32, 025303	3.4	5
130	Evidence of Mechanochemical Control in Grafting to Reactions of Hydroxy-Terminated Statistical Copolymers. <i>Macromolecules</i> , 2021 , 54, 499-508	5.5	3
129	Understanding the Role of Defects in Silicon Nitride-Based Resistive Switching Memories Through Oxygen Doping. <i>IEEE Nanotechnology Magazine</i> , 2021 , 1-1	2.6	3
128	Doping of silicon with phosphorus end-terminated polymers: source characterization and dopant diffusion in SiO ₂ . <i>Journal of Materials Chemistry C</i> , 2021 , 9, 4020-4028	7.1	1
127	Quantification of molecular weight discrimination in reactions from ultrathin polymer films by matrix-assisted laser desorption/ionization time-of-flight mass spectrometry. <i>Analyst, The</i> , 2021 , 146, 6145-6155	5	2
126	Doping of silicon by phosphorus end-terminated polymers: drive-in and activation of dopants. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 10229-10237	7.1	6
125	Thermodynamics and ordering kinetics in asymmetric PS-b-PMMA block copolymer thin films. <i>Soft Matter</i> , 2020 , 16, 5525-5533	3.6	5
124	Effect of Trapped Solvent on the Interface between PS-PMMA Thin Films and P(S-r-MMA) Brush Layers. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 7777-7787	9.5	13
123	Effect of the Density of Reactive Sites in P(S-r-MMA) Film during Al ₂ O ₃ Growth by Sequential Infiltration Synthesis. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900503	4.6	13
122	Thermal Degradation in Ultrathin Films Outperforms Dose Control of n-Type Polymeric Dopants for Silicon. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 1807-1816	4	7
121	Technological strategies for self-assembly of PS-b-PDMS in cylindrical sub-10 nm nanostructures for lithographic applications. <i>Advances in Physics: X</i> , 2018 , 3, 1445558	5.1	4
120	Focus on sub-10 nm nanofabrication. <i>Nanotechnology</i> , 2018 , 29, 260201	3.4	2
119	Trimethylaluminum Diffusion in PMMA Thin Films during Sequential Infiltration Synthesis: In Situ Dynamic Spectroscopic Ellipsometric Investigation. <i>Advanced Materials Interfaces</i> , 2018 , 5, 1801016	4.6	30
118	From grafting to to grafting from 2018 ,		1
117	Ordering kinetics in two-dimensional hexagonal pattern of cylinder-forming PS-b-PMMA block copolymer thin films: Dependence on the segregation strength. <i>Physical Review Materials</i> , 2018 , 2,	3.2	8

116	Electronic band structures of undoped and P-doped Si nanocrystals embedded in SiO ₂ . <i>Journal of Materials Chemistry C</i> , 2018 , 6, 119-126	7.1	7
115	Control of Doping Level in Semiconductors via Self-Limited Grafting of Phosphorus End-Terminated Polymers. <i>ACS Nano</i> , 2018 , 12, 178-186	16.7	19
114	Development and Synchrotron-Based Characterization of Al and Cr Nanostructures as Potential Calibration Samples for 3D Analytical Techniques. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700866	1.6	11
113	Hierarchical Order in Dewetted Block Copolymer Thin Films on Chemically Patterned Surfaces. <i>ACS Nano</i> , 2018 , 12, 7076-7085	16.7	15
112	Effect of Entrapped Solvent on the Evolution of Lateral Order in Self-Assembled P(S-r-MMA)/PS-b-PMMA Systems with Different Thicknesses. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 31215-31223	9.5	13
111	Toward Lateral Length Standards at the Nanoscale Based on Diblock Copolymers. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 15685-15697	9.5	14
110	Nanoscale control of Si nanoparticles within a 2D hexagonal array embedded in SiO thin films. <i>Nanotechnology</i> , 2017 , 28, 014001	3.4	3
109	Doping of silicon nanocrystals. <i>Materials Science in Semiconductor Processing</i> , 2017 , 62, 156-170	4.3	26
108	GISAXS Analysis of the In-Depth Morphology of Thick PS-b-PMMA Films. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 11054-11063	9.5	21
107	Magnetization switching in high-density magnetic nanodots by a fine-tune sputtering process on a large-area diblock copolymer mask. <i>Nanoscale</i> , 2017 , 9, 16981-16992	7.7	8
106	TGA-GCMS quantitative analysis of phosphorus-end capped functional polymers in bulk and ultrathin films. <i>Journal of Analytical and Applied Pyrolysis</i> , 2017 , 128, 238-245	6	10
105	Influence of block copolymer feature size on reactive ion etching pattern transfer into silicon. <i>Nanotechnology</i> , 2017 , 28, 404001	3.4	5
104	High temperature surface neutralization process with random copolymers for block copolymer self-assembly. <i>Polymer International</i> , 2017 , 66, 459-467	3.3	14
103	Molar mass and composition effects on the thermal stability of functional P(S-r-MMA) random copolymers for nanolithographic applications. <i>Molecular Systems Design and Engineering</i> , 2017 , 2, 581-588	4.6	3
102	Ozone-Based Sequential Infiltration Synthesis of AlO Nanostructures in Symmetric Block Copolymer. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 33933-33942	9.5	23
101	CUORE-0 detector: design, construction and operation. <i>Journal of Instrumentation</i> , 2016 , 11, P07009-P07009	10.1	51
100	Synthesis and characterization of P layer in SiO ₂ by monolayer doping. <i>Nanotechnology</i> , 2016 , 27, 075606	9.4	18
99	Composition of ultrathin binary polymer brushes by thermogravimetry-gas chromatography-mass spectrometry. <i>Analytical and Bioanalytical Chemistry</i> , 2016 , 408, 3155-63	4.4	4

98	Evolution of shape, size, and areal density of a single plane of Si nanocrystals embedded in SiO ₂ matrix studied by atom probe tomography. <i>RSC Advances</i> , 2016 , 6, 3617-3622	3.7	13
97	Enhanced Lateral Ordering in Cylinder Forming PS-b-PMMA Block Copolymers Exploiting the Entrapped Solvent. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 8280-8	9.5	17
96	Micrometer-Scale Ordering of Silicon-Containing Block Copolymer Thin Films via High-Temperature Thermal Treatments. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 9897-908	9.5	16
95	Modeling of phosphorus diffusion in silicon oxide and incorporation in silicon nanocrystals. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 3531-3539	7.1	9
94	Thermodynamic stability of high phosphorus concentration in silicon nanostructures. <i>Nanoscale</i> , 2015 , 7, 14469-75	7.7	24
93	Ultrathin random copolymer-grafted layers for block copolymer self-assembly. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 10944-51	9.5	55
92	Fabrication of periodic arrays of metallic nanoparticles by block copolymer templates on HfO ₂ substrates. <i>Nanotechnology</i> , 2015 , 26, 215301	3.4	8
91	Scaling of correlation length in lamellae forming PS-b-PMMA thin films upon high temperature rapid thermal treatments. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 8618-8624	7.1	19
90	Neutral wetting brush layers for block copolymer thin films using homopolymer blends processed at high temperatures. <i>Nanotechnology</i> , 2015 , 26, 415603	3.4	8
89	Resistive switching in high-density nanodevices fabricated by block copolymer self-assembly. <i>ACS Nano</i> , 2015 , 9, 2518-29	16.7	56
88	Thickness and Microdomain Orientation of Asymmetric PS-b-PMMA Block Copolymer Films Inside Periodic Gratings. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 23615-22	9.5	9
87	Thermal stability of functional P(S-r-MMA) random copolymers for nanolithographic applications. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 3920-30	9.5	21
86	Thermally induced self-assembly of cylindrical nanodomains in low molecular weight PS-b-PMMA thin films. <i>Nanotechnology</i> , 2014 , 25, 045301	3.4	25
85	Behavior of phosphorous and contaminants from molecular doping combined with a conventional spike annealing method. <i>Nanoscale</i> , 2014 , 6, 706-10	7.7	36
84	Thermally induced orientational flipping of cylindrical phase diblock copolymers. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 2175-2182	7.1	18
83	Characterization of ultra-thin polymeric films by Gas chromatography-Mass spectrometry hyphenated to thermogravimetry. <i>Journal of Chromatography A</i> , 2014 , 1368, 204-10	4.5	23
82	Ordering dynamics in symmetric PS-b-PMMA diblock copolymer thin films during rapid thermal processing. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 6655-6664	7.1	46
81	Flash grafting of functional random copolymers for surface neutralization. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 4909-4917	7.1	31

80	Fine tuning of lithographic masks through thin films of PS-b-PMMA with different molar mass by rapid thermal processing. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 7180-8	9.5	50
79	Quantification of phosphorus diffusion and incorporation in silicon nanocrystals embedded in silicon oxide. <i>Surface and Interface Analysis</i> , 2014 , 46, 393-396	1.5	16
78	Silicon crystallization in nanodot arrays organized by block copolymer lithography. <i>Journal of Nanoparticle Research</i> , 2014 , 16, 1	2.3	2
77	Evolution of lateral ordering in symmetric block copolymer thin films upon rapid thermal processing. <i>Nanotechnology</i> , 2014 , 25, 275601	3.4	22
76	High aspect ratio PS-b-PMMA block copolymer masks for lithographic applications. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 21389-96	9.5	28
75	Solid-state dewetting of ultra-thin Au films on SiO ₂ and HfO ₂ . <i>Nanotechnology</i> , 2014 , 25, 495603	3.4	35
74	ToF-SIMS study of phosphorus diffusion in low-dimensional silicon structures. <i>Surface and Interface Analysis</i> , 2013 , 45, 386-389	1.5	12
73	Al ₂ O ₃ Passivation on c-si Surfaces for Low Temperature Solar Cell Applications. <i>Energy Procedia</i> , 2013 , 38, 872-880	2.3	0
72	Collective behavior of block copolymer thin films within periodic topographical structures. <i>Nanotechnology</i> , 2013 , 24, 245301	3.4	16
71	On the Thermal Stability of PS-b-PMMA Block and P(S-r-MMA) Random Copolymers for Nanopatterning Applications. <i>Macromolecules</i> , 2013 , 46, 8224-8234	5.5	36
70	Role of oxygen vacancies on the structure and density of states of iron-doped zirconia. <i>Physical Review B</i> , 2013 , 87,	3.3	17
69	Si surface passivation by Al ₂ O ₃ thin films deposited using a low thermal budget atomic layer deposition process. <i>Applied Physics Letters</i> , 2013 , 102, 131603	3.4	23
68	In-plane organization of silicon nanocrystals embedded in SiO ₂ thin films. <i>Nanotechnology</i> , 2013 , 24, 075302	3.4	11
67	Rapid thermal processing of self-assembling block copolymer thin films. <i>Nanotechnology</i> , 2013 , 24, 315601	3.4	63
66	Scaling size of the interplay between quantum confinement and surface related effects in nanostructured silicon. <i>Applied Physics Letters</i> , 2013 , 103, 023103	3.4	30
65	Effective surface passivation of Si surfaces by chemical deposition of (Al ₂ O ₃) _x (B ₂ O ₃) _{1-x} thin layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 701-706	1.6	1
64	Surface passivation for ultrathin Al ₂ O ₃ layers grown at low temperature by thermal atomic layer deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 732-736	1.6	10
63	Fabrication of well-ordered arrays of silicon nanocrystals using a block copolymer mask. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 1477-1484	1.6	4

62	Mechanisms for Substrate-Enhanced Growth during the Early Stages of Atomic Layer Deposition of Alumina onto Silicon Nitride Surfaces. <i>Chemistry of Materials</i> , 2012 , 24, 1080-1090	9.6	15
61	Electronic properties at the oxide interface with silicon and germanium through x-ray induced oxide charging. <i>Applied Physics Letters</i> , 2012 , 101, 211606	3.4	16
60	Superconducting Ga-overdoped Ge layers capped with SiO ₂ : Structural and transport investigations. <i>Physical Review B</i> , 2012 , 85,	3.3	12
59	The energy band alignment of Si nanocrystals in SiO ₂ . <i>Applied Physics Letters</i> , 2011 , 99, 082107	3.4	29
58	The effect of random copolymer on the characteristic dimensions of cylinder-forming PS-b-PMMA thin films. <i>Nanotechnology</i> , 2011 , 22, 185304	3.4	24
57	Structural and electrical properties of Er-doped HfO ₂ and of its interface with Ge (0 0 1). <i>Microelectronic Engineering</i> , 2011 , 88, 415-418	2.5	7
56	The fabrication of tunable nanoporous oxide surfaces by block copolymer lithography and atomic layer deposition. <i>Nanotechnology</i> , 2011 , 22, 335303	3.4	16
55	Stability of Ag nanocrystals synthesized by ultra-low energy ion implantation in SiO ₂ matrices. <i>Journal of Applied Physics</i> , 2011 , 109, 103524	2.5	27
54	Charging phenomena in dielectric/semiconductor heterostructures during x-ray photoelectron spectroscopy measurements. <i>Journal of Applied Physics</i> , 2011 , 110, 053711	2.5	59
53	O ₃ -based atomic layer deposition of hexagonal La ₂ O ₃ films on Si(100) and Ge(100) substrates. <i>Journal of Applied Physics</i> , 2010 , 108, 084108	2.5	28
52	Microdomain orientation dependence on thickness in thin films of cylinder-forming PS-b-PMMA. <i>Nanotechnology</i> , 2010 , 21, 185304	3.4	31
51	Dielectric properties of Er-doped HfO ₂ (Er~15%) grown by atomic layer deposition for high- ϵ_r gate stacks. <i>Applied Physics Letters</i> , 2010 , 96, 182901	3.4	36
50	Si nanocrystal synthesis in HfO ₂ /SiO ₂ /HfO ₂ multilayer structures. <i>Nanotechnology</i> , 2010 , 21, 055606	3.4	15
49	Phosphorus doping of ultra-small silicon nanocrystals. <i>Nanotechnology</i> , 2010 , 21, 025602	3.4	62
48	Rare earth-based high-k materials for non-volatile memory applications. <i>Microelectronic Engineering</i> , 2010 , 87, 290-293	2.5	9
47	Interface Study in a "Metal / High-k" Gate Stack: Tantalum Nitride on Hafnium Oxide. <i>ECS Transactions</i> , 2009 , 16, 99-110	1	3
46	Chemical and Structural Properties of a TaN/HfO ₂ Gate Stack Processed Using Atomic Vapor Deposition. <i>Journal of the Electrochemical Society</i> , 2009 , 156, G78	3.9	6
45	Poly(3-hexylthiophene)/ZnO hybrid pn junctions for microelectronics applications. <i>Applied Physics Letters</i> , 2009 , 94, 143501	3.4	69

44	Thermally induced permittivity enhancement in La-doped ZrO ₂ grown by atomic layer deposition on Ge(100). <i>Applied Physics Letters</i> , 2009 , 95, 122902	3.4	30
43	Detrimental impact of technological processes on BTI reliability of advanced high-K/metal gate stacks. <i>Reliability Physics Symposium, 2009 IEEE International</i> , 2009 ,		7
42	Atomic Layer Deposition of NiO Films on Si(100) Using Cyclopentadienyl-Type Compounds and Ozone as Precursors. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H807	3.9	36
41	Energy band alignment at TiO ₂ /Si interface with various interlayers. <i>Journal of Applied Physics</i> , 2008 , 103, 043509	2.5	52
40	Effect of oxygen on the electronic configuration of Gd ₂ O ₃ /Ge heterojunctions. <i>Applied Physics Letters</i> , 2008 , 92, 042106	3.4	16
39	Resistance switching in amorphous and crystalline binary oxides grown by electron beam evaporation and atomic layer deposition. <i>Microelectronic Engineering</i> , 2008 , 85, 2414-2419	2.5	52
38	Study of the interfaces in resistive switching NiO thin films deposited by both ALD and e-beam coupled with different electrodes (Si, Ni, Pt, W, TiN). <i>Microelectronic Engineering</i> , 2008 , 85, 2425-2429	2.5	22
37	Atomic oxygen-assisted molecular beam deposition of Gd ₂ O ₃ films for ultra-scaled Ge-based electronic devices. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 236-240	4.3	9
36	XPS and IPE analysis of HfO ₂ band alignment with high-mobility semiconductors. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 221-225	4.3	16
35	Evidence for a dose dependence for thermal redistribution of implanted silicon in SiO ₂ . <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 254, 139-142	1.2	1
34	Understanding of the thermal stability of the hafnium oxide/TiN stack via 2 High k and 2 metal deposition techniques. <i>Microelectronic Engineering</i> , 2007 , 84, 1886-1889	2.5	13
33	Oxide-nitride-oxide memory stacks formed by low-energy Si ion implantation into nitride and wet oxidation. <i>Microelectronic Engineering</i> , 2007 , 84, 1986-1989	2.5	4
32	Wet oxidation of nitride layer implanted with low-energy Si ions for improved oxide-nitride-oxide memory stacks. <i>Applied Physics Letters</i> , 2007 , 90, 263513	3.4	8
31	Conductive-filament switching analysis and self-accelerated thermal dissolution model for reset in NiO-based RRAM 2007 ,		80
30	Conduction band offset of HfO ₂ on GaAs. <i>Applied Physics Letters</i> , 2007 , 91, 192902	3.4	44
29	Fabrication of GeO ₂ layers using a divalent Ge precursor. <i>Applied Physics Letters</i> , 2007 , 90, 162115	3.4	80
28	The interface between Gd ₂ O ₃ films and Ge(001): A comparative study between molecular and atomic oxygen mediated growths. <i>Journal of Applied Physics</i> , 2007 , 102, 034513	2.5	12
27	Atomic Layer Deposition of Magnetic Thin Films. <i>Acta Physica Polonica A</i> , 2007 , 112, 1271-1280	0.6	18

26	Nanocrystals in High-k Dielectric Stacks for Non-Volatile Memory Applications. <i>Advances in Science and Technology</i> , 2006 , 51, 156-166	0.1	7
25	Materials Science Issues for the Fabrication of Nanocrystal Memory Devices by Ultra Low Energy Ion Implantation. <i>Defect and Diffusion Forum</i> , 2006 , 258-260, 531-541	0.7	6
24	Energy band alignment of HfO ₂ on Ge. <i>Journal of Applied Physics</i> , 2006 , 100, 093718	2.5	37
23	X-ray photoelectron spectroscopy study of energy-band alignments of Lu ₂ O ₃ on Ge. <i>Surface and Interface Analysis</i> , 2006 , 38, 494-497	1.5	25
22	Synthesis of mono and bi-layer of Si nanocrystals embedded in a dielectric matrix by e-beam evaporation of SiO/SiO ₂ thin films. <i>Materials Science and Engineering C</i> , 2006 , 26, 835-839	8.3	6
21	Comparative study of negative cluster emission in sputtering of Si, Ge and their oxides. <i>Applied Surface Science</i> , 2006 , 252, 7236-7238	6.7	1
20	Interstitial injection during oxidation of very low energy nitrogen-implanted silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 124-125, 314-318	3.1	1
19	Negative cluster emission in sputtering of Si _{1-x} Ge _x alloys: A full spectrum approach. <i>Surface Science</i> , 2005 , 599, 141-149	1.8	12
18	Fabrication of nanocrystal memories by ultra low energy ion implantation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1907-1911		4
17	Oxidation-enhanced diffusion of boron in very low-energy N ₂ ⁺ -implanted silicon. <i>Journal of Applied Physics</i> , 2005 , 97, 113534	2.5	5
16	Oxidation of nitrogen-implanted silicon: Comparison of nitrogen distribution and electrical properties of oxides formed by very low and medium energy N ₂ ⁺ implantation. <i>Journal of Applied Physics</i> , 2004 , 96, 300-309	2.5	7
15	Detection and characterization of silicon nanocrystals embedded in thin oxide layers. <i>Journal of Applied Physics</i> , 2004 , 95, 257-262	2.5	51
14	Manipulation of 2D arrays of Si nanocrystals by ultra-low-energy ion beam-synthesis for nonvolatile memories applications. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 830, 219		0
13	Nitrogen distribution during oxidation of low and medium energy nitrogen-implanted silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 216, 75-79	1.2	
12	Nanocrystals manufacturing by ultra-low-energy ion-beam-synthesis for non-volatile memory applications. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 216, 228-238	1.2	38
11	Silicon nanocrystal memory devices obtained by ultra-low-energy ion-beam synthesis. <i>Solid-State Electronics</i> , 2004 , 48, 1511-1517	1.7	61
10	Characterization of silicon nanocrystals embedded in thin oxide layers by TOF-SIMS. <i>Applied Surface Science</i> , 2004 , 231-232, 813-816	6.7	15
9	Manipulation of two-dimensional arrays of Si nanocrystals embedded in thin SiO ₂ layers by low energy ion implantation. <i>Journal of Applied Physics</i> , 2004 , 95, 5696-5702	2.5	111

8	Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs ⁺ sputtering in negative mode by ToF-SIMS: a full spectrum approach. <i>Applied Surface Science</i> , 2003 , 203-204, 52-55	6.7	25
7	Nanocrystals depth profiling by means of Cs ⁺ in negative polarity with dual beam ToF-SIMS. <i>Applied Surface Science</i> , 2003 , 203-204, 110-113	6.7	5
6	Silicon self-diffusivity measurement in thermal SiO ₂ by ³⁰ Si/ ²⁸ Si isotopic exchange. <i>Journal of Applied Physics</i> , 2003 , 94, 2136-2138	2.5	31
5	Time of flight secondary ion mass spectrometry study of silicon nanoclusters embedded in thin silicon oxide layers. <i>Applied Physics Letters</i> , 2003 , 82, 121-123	3.4	24
4	Depth positioning of silicon nanoparticles created by Si ULE implants in ultrathin SiO ₂ 2002 ,		1
3	Characterization of gate oxynitrides by means of time of flight secondary ion mass spectrometry and x-ray photoelectron spectroscopy. Quantification of nitrogen. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002 , 20, 616-621	2.9	9
2	Experimental Determination of the Band Offset of Rare Earth Oxides on Various Semiconductors 269-283		4
1	Influence of spin casting solvent on the self-assembly of silicon-containing block copolymer thin films via high temperature thermal treatment. <i>Polymer International</i> ,	3.3	1